Data Sheet No. PD-3.065
49C 04734 D

INTERNATIONAL RECTIFIER IOR

T-25-20

1180A RMS Fast Turn-Off Hockey Puk Thyristors

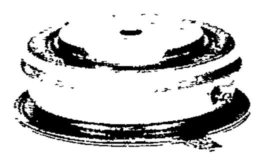
750PEF SERIES

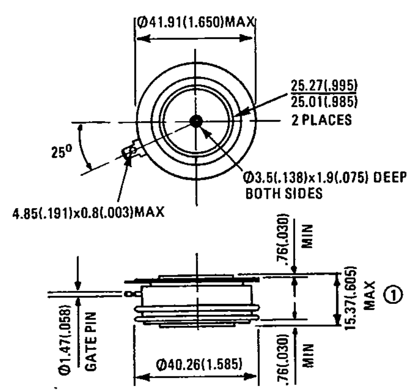
Description

The 750PEF series of fast turn-off thyristors use centre amplified gate junction technology. These devices with their inherently fast switching characteristics combined with their excellent turn-off capabilities will find applications in inverters for UPS systems, AC motor drives, induction heating and choppers.

Features

- Centre Amplified Gate
- High di/dt and dv/dt capabilities
- High frequency operation
- Low switching losses
- High Surge capabilities
- Available up to 600V V_{RRM}, V_{DRM}
- Fully characterised information
- Choice of turn-off time specification





All dimensions in millimeters and (inches)
① - clamped dimension

Major ratings and characteristics

		750PEF......	Units
$I_{T(AV)}$		750	A
$I_{T(RMS)}$		1180	A
I_{TSM}	50Hz	7100	A
	60Hz	7450	A
I^2t	50Hz	252,000	A^2s
	60Hz	230,000	A^2s
$I^2\sqrt{t}$		3 610 000	$A^2\sqrt{s}$
t_q		8	μs
V_{RRM}		100 to 600	V
T_J		−40 to 125	°C

ELECTRICAL SPECIFICATIONS

Forward conduction

		750PEF......		Units	Conditions		
$I_{T(AV)}$	Maximum average on-state current	750		A	180° conduction, half-sine wave, T_c = 55°C		
$I_{T(RMS)}$	Nominal continuous RMS on-state current	1180		A			
I_{TRM}	Maximum peak repetitive on-state current	6950		A	30° sinusoidal conduction, T_c = 62°C		
	Mounting force ± 10%	8920(2000)	4460(1000)	N(lbf)			
I_{TSM}	Maximum peak, one cycle non repetitive on-state current	8500	8000	A	t = 10ms	No voltage reapplied	Sinusoidal half-wave Initial T_J = 125°C
		8900	8400	A	t = 8.3ms		
		7100	6700	A	t = 10ms	100% V_{RRM} reapplied	
		7450	7050	A	t = 8.3ms		
I^2t	Maximum I^2t for fusing	361 000	320 000	A^2s	t = 10ms	No voltage reapplied	Initial T_J = 125°C
		328 000	292 000	A^2s	t = 8.3ms		
		252 000	226 000	A^2s	t = 10ms	100% V_{RRM} reapplied	
		230 000	206 000	A^2s	t = 8.3ms		
$I^2\sqrt{t}$	Maximum $I^2\sqrt{t}$ for fusing	3 610 000	3 200 000	$A^2\sqrt{s}$	t = 0.1 – 10ms, no voltage reapplied		
V_{TM}	Maximum peak on-state voltage	2.20		V	T_J = 25°C, 180° conduction, I_{TM} = TLxIT(AV)(2355 Apeak)		
di/dt	Maximum non-repetitive rate of rise of turned on current	800		A/µs	JEDEC STD RS–397, 5 2.2.6.: T_c = 125°C, V_{DM} = V_{DRM}, I_{TM} = 1600A gate source 20V open circuit 20Ω t_r = 0.5µs, t_p = 20µs.		
I_H	Maximum holding current	600		mA	T_J = 25°C, anode supply = 6V, resistive load, gate open circuit		
I_L	Maximum latching current	1000		mA	T_J = 25°C, anode supply = 6V, resistive load		

Triggering

P_{GM}	Maximum peak gate power	10	W	$t_p \leq 5ms$	
$P_{G(AV)}$	Maximum average gate power	2	W		
I_{GM}	Maximum peak gate current	3	A		
V_{GM}	Maximum peak gate voltage	20	V		
$-V_{GM}$	Maximum peak negative gate voltage	5	V		
V_{GT}	Maximum gate voltage required to trigger	3.0	V	T_J = –40°C	Anode supply = 6V resistive load
		2.5	V	T_J = 25°C	
		1.7	V	T_J = 125°C	
I_{GT}	Maximum gate current required to trigger	400	mA	T_J = –40°C	Anode supply = 6V resistive load
		200	mA	T_J = 25°C	
		150	mA	T_J = 125°C	
V_{GD}	Maximum gate voltage that will not trigger	0.20	V	T_J = 125°C, rated V_{DRM} applied	

Switching

t_d	Maximum delay time	1.3	µs	T_J = 25°C, V_D = 0.8 V_{DRM}, I_{TM} = 260A, gate source 20V open circuit, R_{source} = 20Ω, resistive load t_r (pulse rise time) 0.5µs, t_p = 20µs
t_q	Turn-off time	See separate table		
$t_{q(diode)}$	Typical turn-off time with anti parallel diode	20% more than with $V_R \geq 50V$; see separate table.	µs	T_J = 125°C, I_{TM} = 500A for 200µs, V_R = 1V, di/dt = –25 A/µs reapplied dv/dt = 200V/µs linear to 0.8 V_{DRM}, V_g = 0V, R_{gk} = 100 Ω
Q_{rr}	Typical stored charge	35	µc	T_J = 125°C, I_{TM} = 400A, –di/dt = 100 A/µs

Blocking

dv/dt	Minimum critical rate of rise of off-state voltage	500	V/µs	T_J = 125°C, linear to 0.8 V_{DRM}, gate open circuit

Voltage ratings

Part number	V_{RRM}, maximum repetitive peak reverse voltage $V_g \leq 0$ T_J = –40 to 125°C	V_{RSM}, maximum non repetitive peak reverse voltage. T_J = 25 to 125°C	V_{DRM}, maximum repetitive peak off-state voltage, gate open circuit T_J = -40°C to 125°C	I_{RM}, I_{DM}, maximum peak reverse and off-state leakage current at V_{RRM}, V_{DRM}, T_J = 125°C, gate open circuit
	V	V	V	mA
750PEF10...	100	200	100	30
750PEF20...	200	300	200	30
750PEF40...	400	500	400	30
750PEF60...	600	700	600	30

THERMAL AND MECHANICAL SPECIFICATIONS

			750PEF......		Units	Conditions
T_J	Junction operating temperature range		−40 to 125		°C	
T_{stg}	Storage temperature range		−40 to 150		°C	
R_{thJC}	Maximum thermal impedance, junction to case.	Single side cooled	0.08		K/W	DC Operation
		Double side cooled	0.04		K/W	
R_{thCS}	Maximum thermal resistance, one pole piece to one heat exchanger		0.04 (0.05)	0.03 (0.04)	K/W	Mounting surface smooth flat and greased (JEDEC STD RS–397, 7.9.4)
	Mounting force ± 10%		1000	2000	lbf	
			4460	8920	N	
W	Approximate weight		3		oz	
			85		g	

TURN-OFF TIME TABLE

Part number	Turn-off code	tq Turn-off time		Units	Conditions	
		typical	max			
750PEF. .V..	08	6	8	μs	reapplied dv/dt = 20V/μs linear to 0.8 V_{DRM}	T_J = 125°C, I_{TM} = 500A for 200μs V_R = 50V di/dt = −25A/μs V_g = 0V R_{gk} = 100Ω
	10	8	10	μs		
	12	9	12	μs		
750PEF...W..	12	9	12	μs	reapplied dv/dt = 200V/μs linear to 0 8 V_{DRM}	
	15	11	15	μs		
	18	14	18	μs		

CODING

To complete code add $V_{RRM}/10$ and required turn-off code i.e. for 750PEF...... with V_{RRM} = 400V and t_q = 12μs with reapplied dv/dt = 200V/μs complete part number is 750PEF40W12, but for 750PEF...... with same parameters except reapplied dv/dt = 20V/μs complete part number is 750PEF40V12.

INDEX TO GRAPHS

Use of the Heatsink Selection Nomogram

These nomograms may be used to obtain rapidly the required sink to ambient thermal resistance for a particular application. The example shows the method.

From the starting point A, the known average on-state current, proceed to point 'B', the operating conduction angle. At this point the maximum average power dissipation may be read off at C. If the maximum ambient temperature is known, proceed vertically from this figure at point E to cross the extension of line C–B at D. The thermal impedance may now be found by taking the lines on either side of point D and choosing the lower figure or by interpolation. The final figure is then found by subtracting the ΔR figure appropriate to the conduction angle in the right hand table.

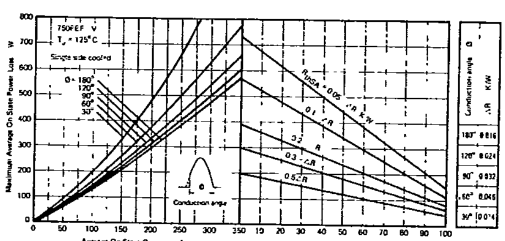
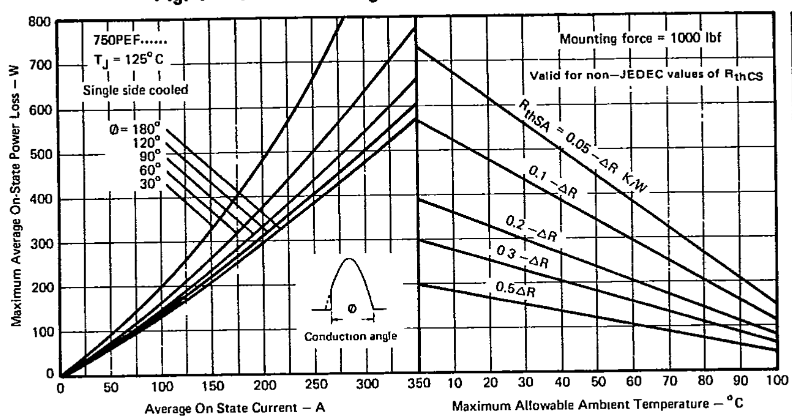
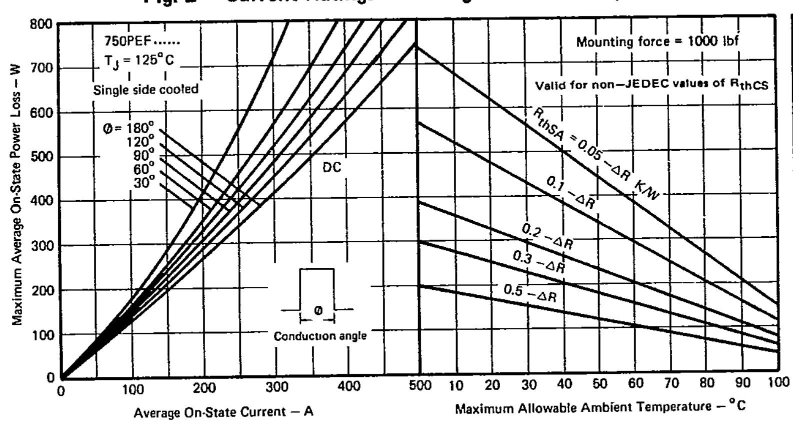


Fig. 1 — Current Ratings — sinusoidal waveforms, 50—400Hz



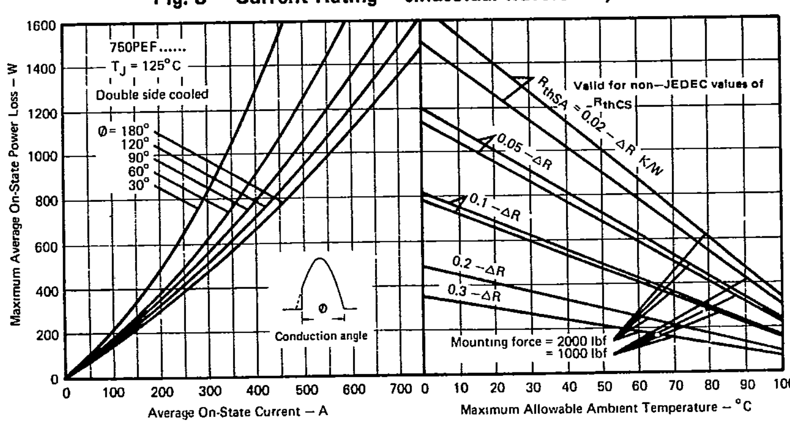
Conduction angle – Ø	ΔR – K/W
180°	0.016
120°	0.024
90°	0.032
60°	0.046
30°	0.074

Fig. 2 — Current Ratings — rectangular waveforms, 50—400Hz



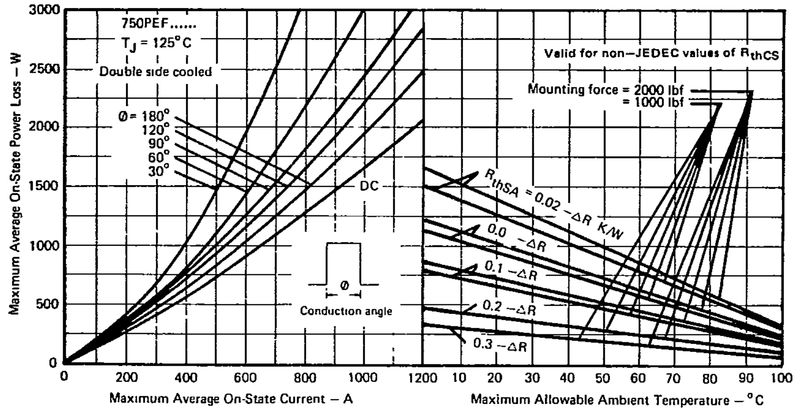
Conduction angle – Ø	ΔR – K/W
DC	0
180°	0.011
120°	0.016
90°	0.022
60°	0.030
30°	0.051

Fig. 3 — Current Rating — sinusoidal waveforms, 50—400Hz



Conduction angle – Ø	ΔR – K/W
180°	0.008
120°	0.012
90°	0.016
60°	0.023
30°	0.037

Fig. 4 — Current Ratings — rectangular waveforms, 50—400Hz



Conduction angle — Ø	ΔR — K/W
DC	0
180°	0.0056
120°	0.008
90°	0.011
60°	0.015
30°	0.025

Fig. 5 — Case Temperature Ratings

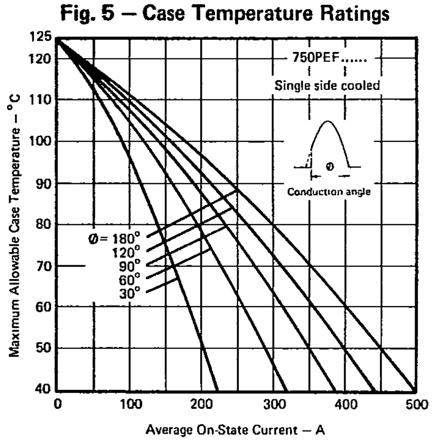


Fig. 6 — Case Temperature Ratings

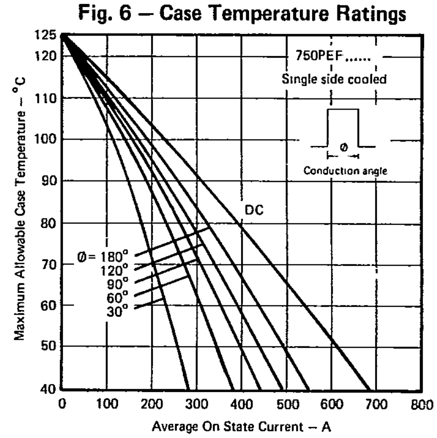


Fig. 7 — Case Temperature Ratings

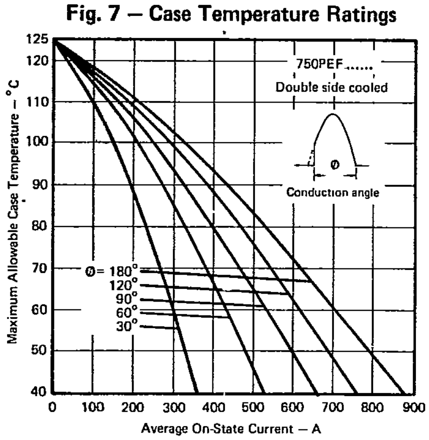


Fig. 8 — Case Temperature Ratings

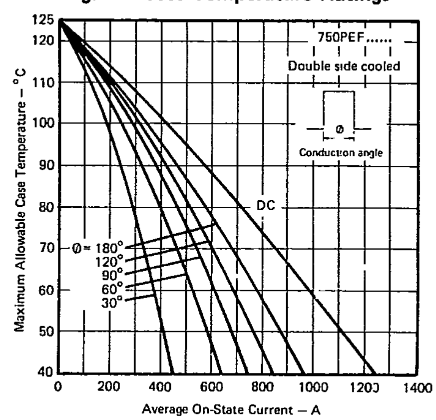


Fig. 9 — Power Loss Characteristics

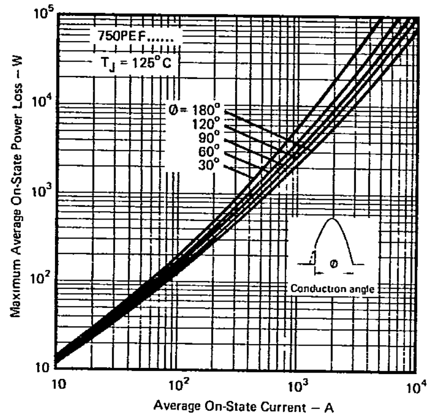


Fig. 10 — Power Loss Characteristics

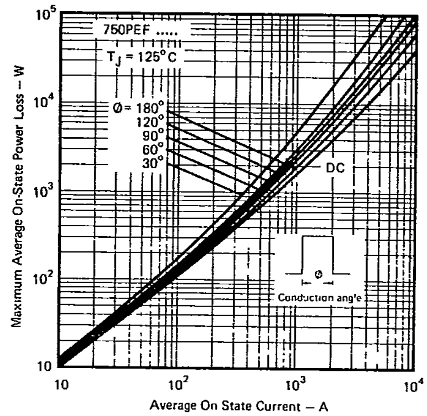


Fig. 11 — On-State Characteristics

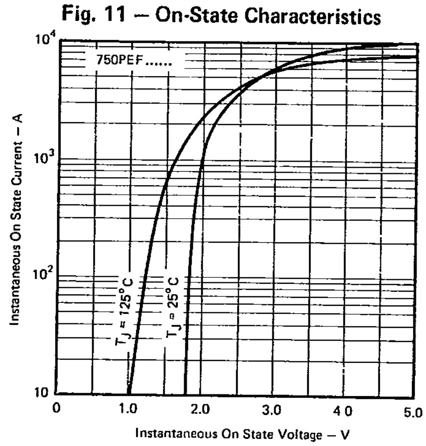


Fig. 12 — Energy Loss per Pulse Characteristics — sinusoidal waveforms

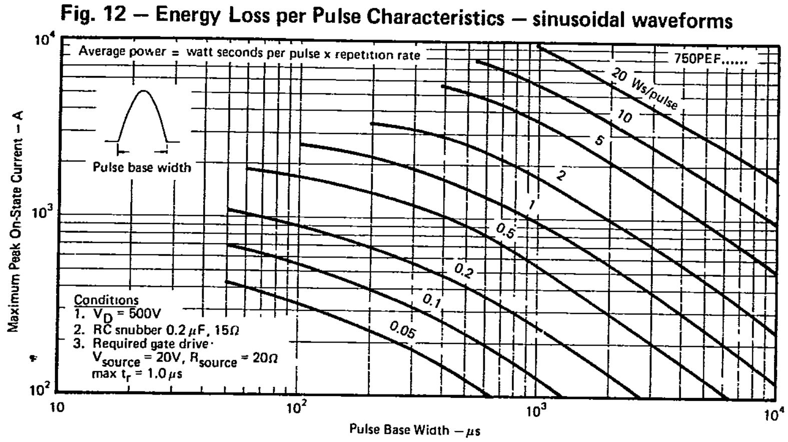


Fig. 13 — Energy Loss per Pulse Characteristics — trapezoidal waveforms

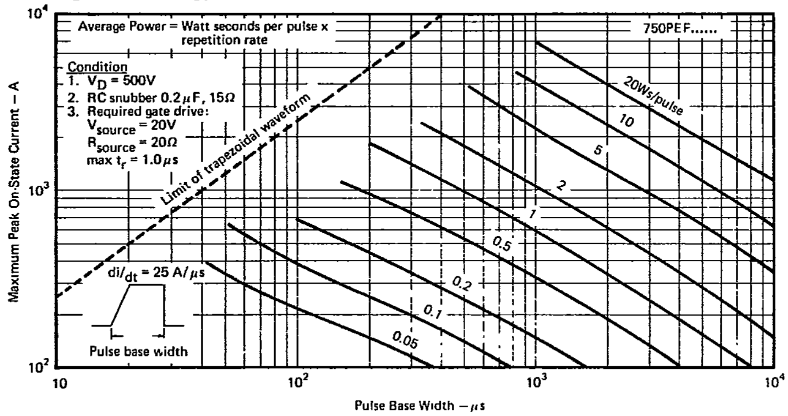


Fig. 14 — Energy Loss per Pulse Characteristics — trapezoidal waveforms

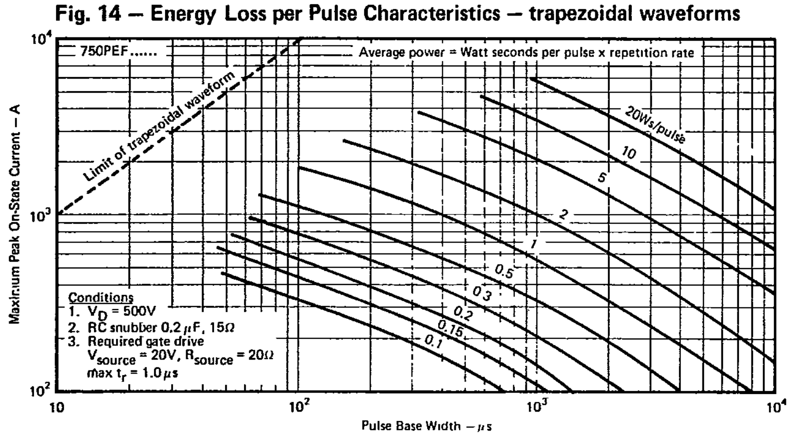


Fig. 15 — Peak On-State Current vs Pulse Width — sinusoidal waveforms

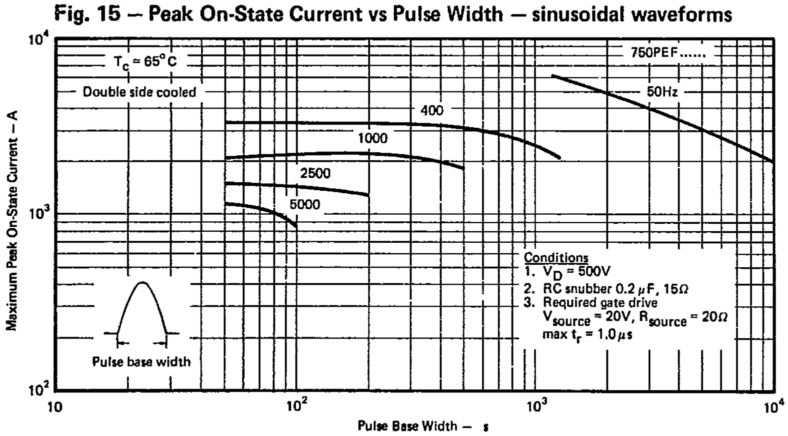


Fig. 16 — Peak On-State Current vs Pulse Width — sinusoidal waveforms

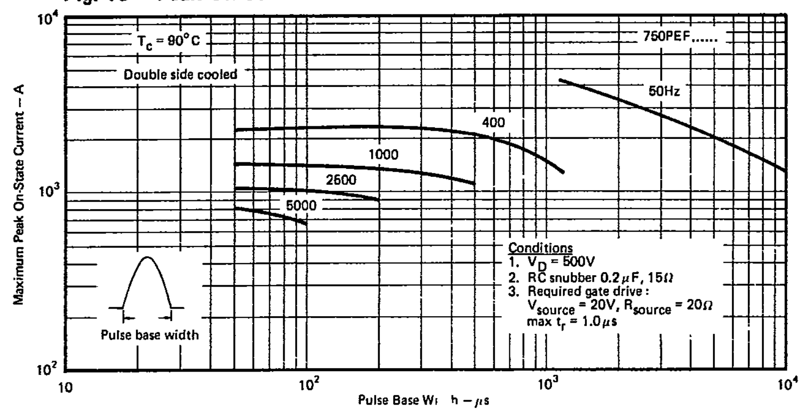


Fig. 17 — Peak On-State Current vs di/dt — trapezoidal waveforms

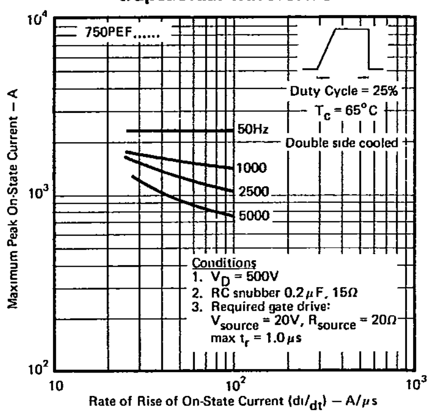


Fig. 18 — Peak On-State Current vs di/dt — trapezoidal waveforms

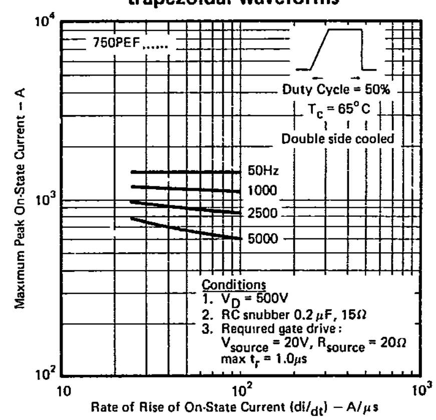


Fig. 19 — Peak On-State Current vs di/dt — trapezoidal waveforms

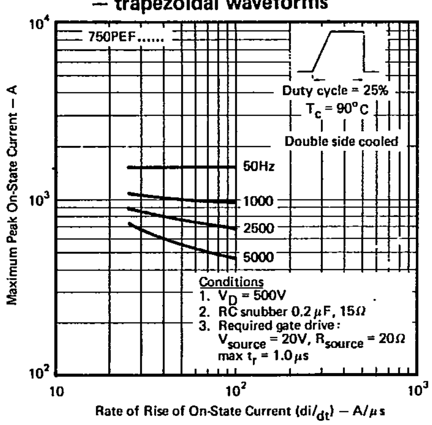


Fig. 20 — Peak On-State Current vs di/dt — trapezoidal waveforms

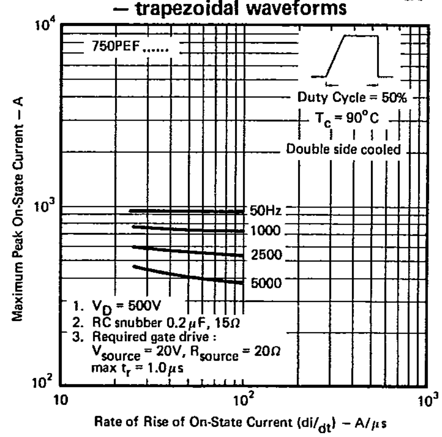


Fig. 21 — Peak On-State Current vs Frequency — sinusoidal waveforms

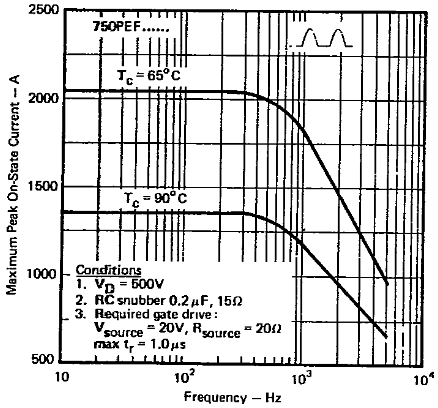


Fig. 22 — Peak On-State Current vs Frequency — trapezoidal waveforms

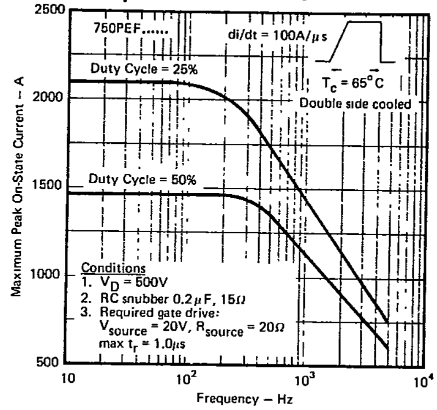


Fig. 23 — Peak On-State Current vs Frequency — trapezoidal waveforms

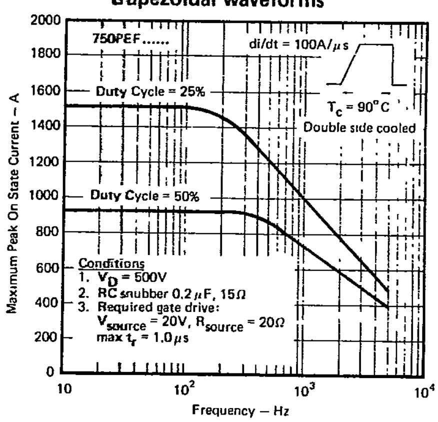


Fig. 24 — Gate Characteristics

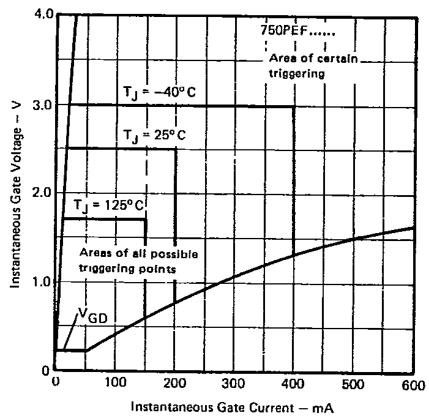


Fig. 25 — Transient Thermal Impedance

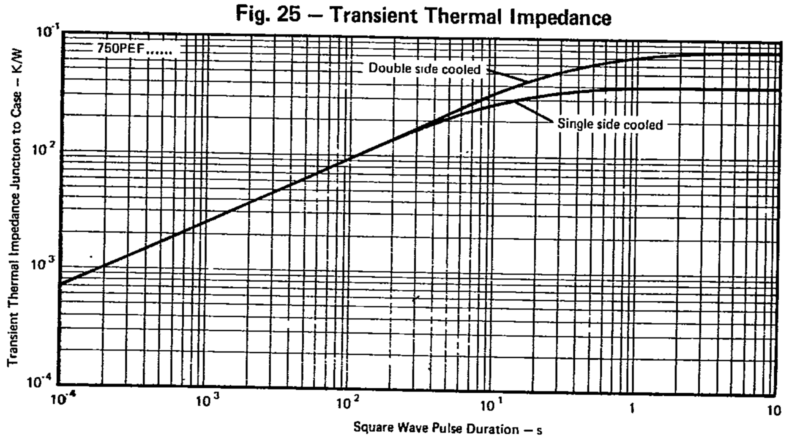


Fig. 26 — Non-Repetitive Surge Ratings

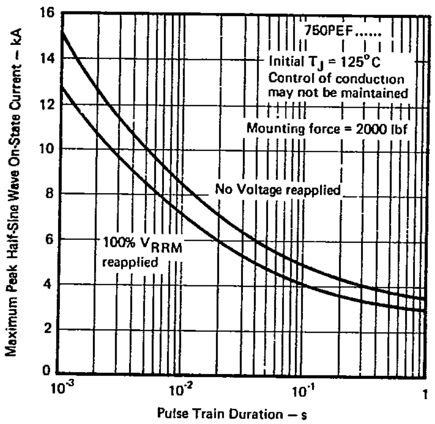


Fig. 27 — Non-Repetitive Surge Ratings

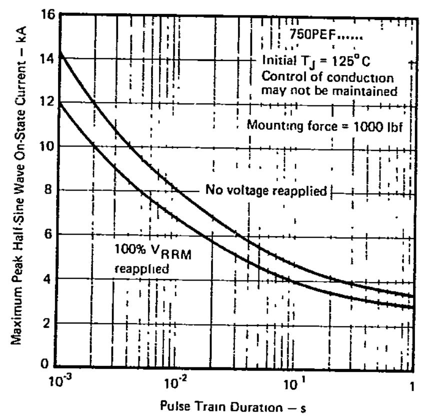


Fig. 28 — Typical Stored Charge Characteristics — sinusoidal waveforms

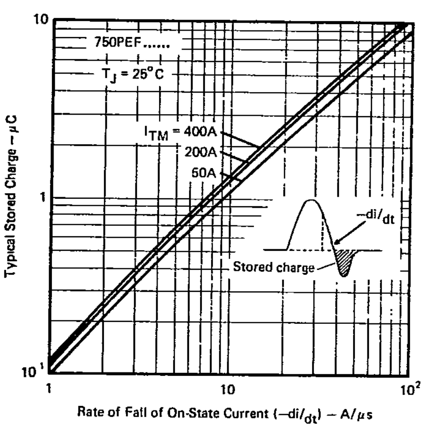
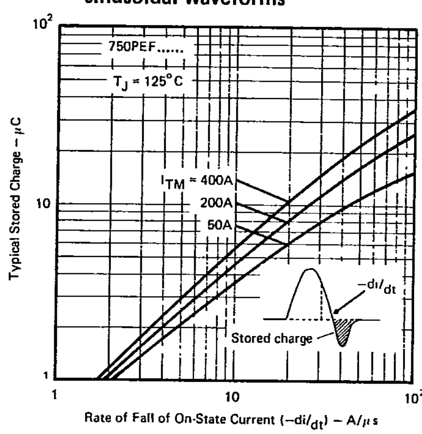


Fig. 29 — Typical Stored Charge Characteristics — sinusoidal waveforms



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